1.8V Drive Nch MOSFET

RUM003N02

●Structure

Silicon N-channel MOSFET

Applications

Switching

● Features

- 1) Low on-resistance.
- 2) Fast switching speed.
- 3) Low voltage drive (1.8V) makes this device ideal for portable equipment.
- 4) Drive circuits can be simple.
- 5) Parallel use is easy.

Packaging specifications

Туре	Package	Taping				
	Code	T2L				
	Basic ordering unit (pieces)	8000				
RUM00	0					

● Absolute maximum ratings (Ta=25°C)

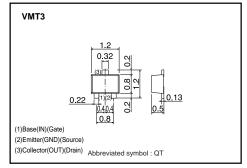
Parameter		Symbol	Limits	Unit
Drain-source voltage		VDSS	20	V
Gate-source voltage		Vgss	±8	V
Drain current	Continuous	ΙD	±300	mA
	Pulsed	IDP*1	±600	mA
Total power dissipation		Pp*2	150	mW
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	-55 to +150	°C

^{*1} Pw≤10μs, Duty cycle≤1%

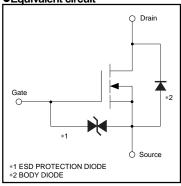
●Thermal resistance

Parameter	Symbol	Limits	Unit	
Channel to ambient	Rth(ch-a)*	833	°C/W	
* Each terminal mounted on a recommended land				

●Dimensions (Unit:mm)



●Equivalent circuit



^{*2} Each terminal mounted on a recommended land

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	Igss	-	-	10	μΑ	Vgs=±8V, Vps=0V
Drain-source breakdown voltage	V(BR)DSS	20	-	-	V	In=1mA, Vgs=0V
Zero gate voltage drain current	Ipss	-	-	1.0	μΑ	V _{DS} =20V, V _{GS} =0V
Gate threshold voltage	VGS(th)	0.3	-	1.0	V	VDS=10V, ID=1mA
Static drain-source on-state resistance		-	0.7	1.0	Ω	In=300mA, Vgs=4.0V
	RDS(on)*	-	8.0	1.2	Ω	In=300mA, Vgs=2.5V
		-	1.0	1.4	Ω	In=300mA, Vgs=1.8V
Forward transfer admittance	Yfs *	400	-	-	ms	In=300mA, Vns=10V
Input capacitance	Ciss	-	25	-	pF	V _{DS} =10V
Output capacitance	Coss	-	10	-	pF	Vgs=0V
Reverse transfer capacitance	Crss	-	10	-	pF	f=1MHz
Turn-on delay time	td(on) *	-	5	-	ns	ID=150mA, VDD ≒10V
Rise time	tr *	-	10	-	ns	V _G s=4.0V
Turn-off delay time	td(off) *	-	15	-	ns	RL=67Ω
Fall time	tr *	-	10	-	ns	R _G =10Ω

^{*} Pulsed

●Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsp*	-	-	1.2	V	I _S = 100mA, V _{GS} =0V

^{*} Pulsed

•Electrical characteristic curves

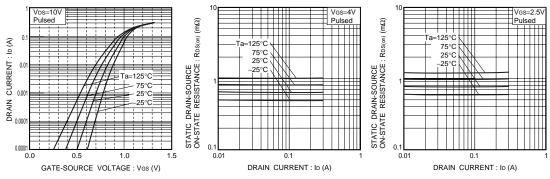


Fig.1 Typical transfer characteristics

Fig.2 Static drain-source on-state resistance vs. drain current (I)

Fig.3 Static drain-source on-state resistance vs. drain current (II)

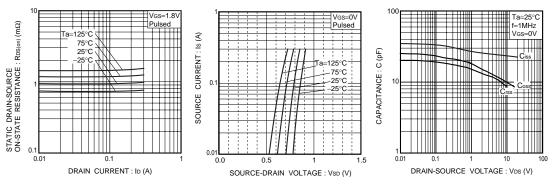


Fig.4 Static drain-source on-state resistance vs. drain current (III)

Fig.5 Source current vs. source-drain voltage

Fig.6 Typical capacitance vs. drain-source voltage

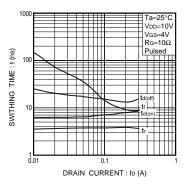


Fig.7 Switching characteristics

•Switching characteristics measurement circuit

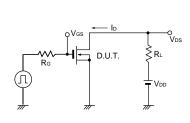


Fig.8 Switching time measurement circuit

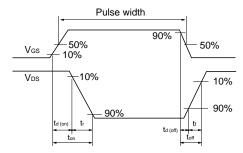


Fig.9 Switching time waveforms

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Appendix1-Rev2.0